

Standard Rectifier Module


3~ Rectifier	
V_{RRM}	= 1600 V
I_{DAV}	= 90 A
I_{FSM}	= 750 A

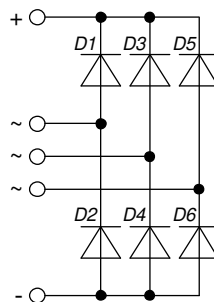
3~ Rectifier Bridge

Part number

VUO82-16NO7



 E72873



Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications:

- Diode for main rectification
- For three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Package: PWS-D

- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Easy to mount with two screws
- Base plate: Copper internally DCB isolated
- Advanced power cycling

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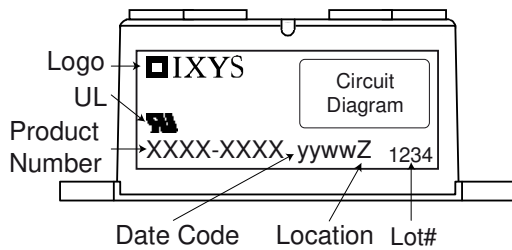
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Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage					1700	V
V_{RRM}	max. repetitive reverse blocking voltage					1600	V
I_R	reverse current	$V_R = 1600$ V		$T_{VJ} = 25^\circ\text{C}$		100	μA
		$V_R = 1600$ V		$T_{VJ} = 150^\circ\text{C}$		1.5	mA
V_F	forward voltage drop	$I_F = 30$ A		$T_{VJ} = 25^\circ\text{C}$		1.08	V
		$I_F = 90$ A				1.35	V
		$I_F = 30$ A		$T_{VJ} = 125^\circ\text{C}$		0.99	V
		$I_F = 90$ A				1.33	V
I_{DAV}	bridge output current	$T_C = 115^\circ\text{C}$	rectangular	$T_{VJ} = 150^\circ\text{C}$		90	A
			$d = \frac{1}{3}$				
V_{FO}	threshold voltage	} for power loss calculation only		$T_{VJ} = 150^\circ\text{C}$		0.78	V
r_F	slope resistance					6	m Ω
R_{thJC}	thermal resistance junction to case					0.9	K/W
R_{thCH}	thermal resistance case to heatsink					0.4	K/W
P_{tot}	total power dissipation			$T_C = 25^\circ\text{C}$		135	W
I_{FSM}	max. forward surge current	$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 45^\circ\text{C}$		750	A
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		810	A
		$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 150^\circ\text{C}$		640	A
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		690	A
I^2t	value for fusing	$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 45^\circ\text{C}$		2.82	kA ² s
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		2.73	kA ² s
		$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 150^\circ\text{C}$		2.05	kA ² s
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		1.98	kA ² s
C_J	junction capacitance	$V_R = 400$ V; $f = 1$ MHz		$T_{VJ} = 25^\circ\text{C}$		27	pF

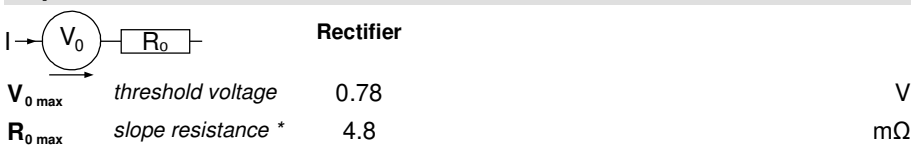


Package PWS-D			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			150	A
T_{VJ}	virtual junction temperature		-40		150	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		125	°C
Weight				159		g
M_D	mounting torque		4.25		5.75	Nm
M_T	terminal torque		4.25		5.75	Nm
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	9.5			mm
$d_{Spb/Apb}$		terminal to backside	26.0			mm
V_{ISOL}	isolation voltage	t = 1 second	3000			V
		t = 1 minute	2500			V



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VUO82-16NO7	VUO82-16NO7	Box	10	504848

Equivalent Circuits for Simulation * on die level $T_{VJ} = 150^{\circ}C$



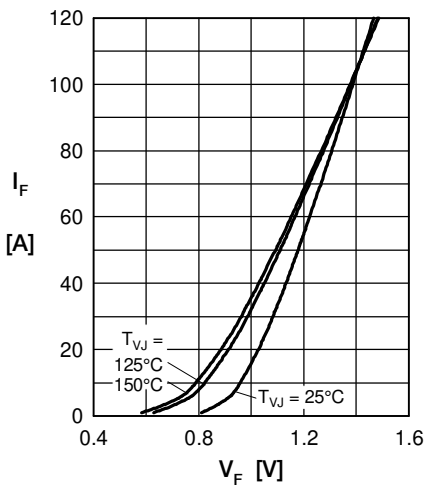
Rectifier


Fig. 1 Forward current versus voltage drop per diode

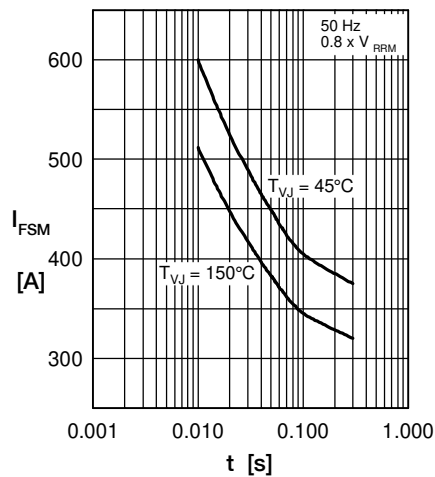


Fig. 2 Surge overload current

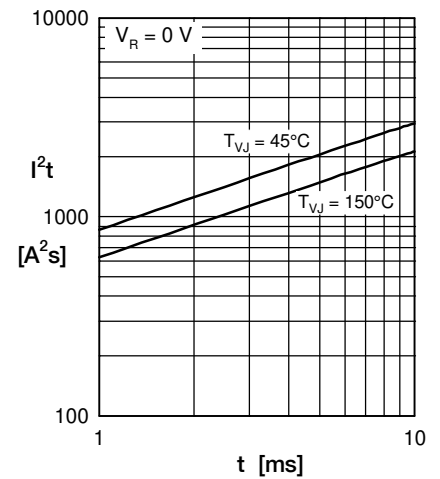
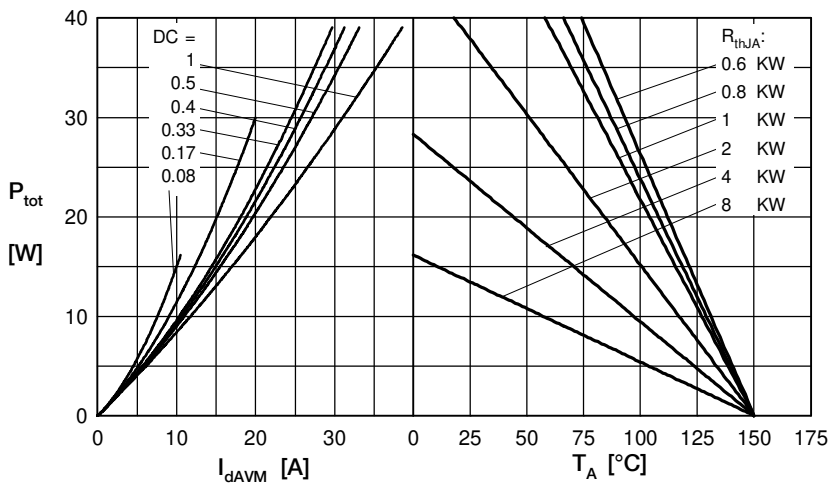

 Fig. 3 I^2t versus time per diode


Fig. 4 Power dissipation vs. direct output current & ambient temperature

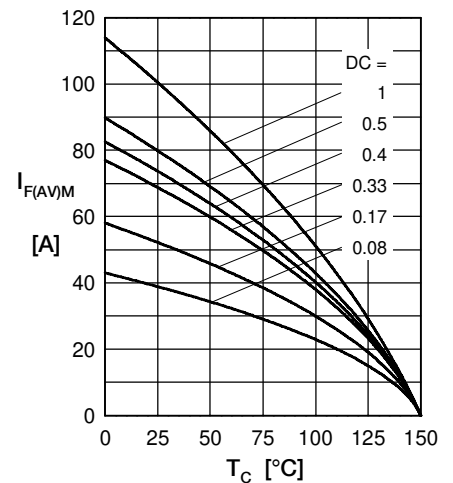


Fig. 5 Max. forward current vs. case temperature

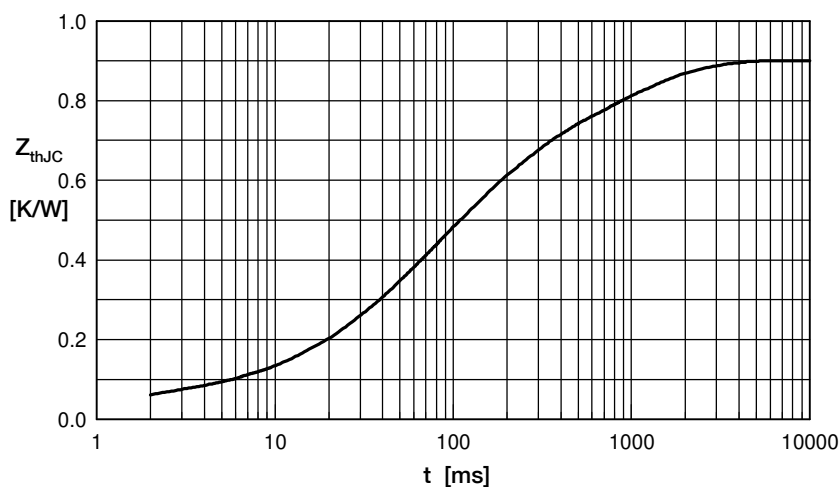


Fig. 6 Transient thermal impedance junction to case

 Constants for Z_{thJC} calculation:

i	R_{th} (K/W)	t_i (s)
1	0.05	0.001
2	0.14	0.030
3	0.18	0.070
4	0.28	0.150
5	0.25	0.950